

FIG. 1

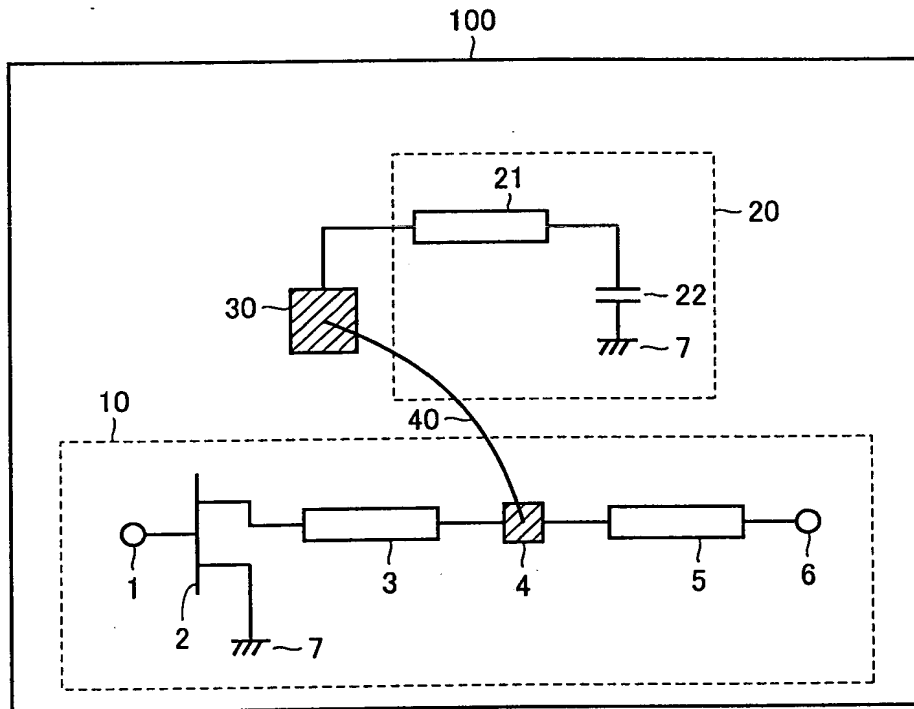


FIG. 2

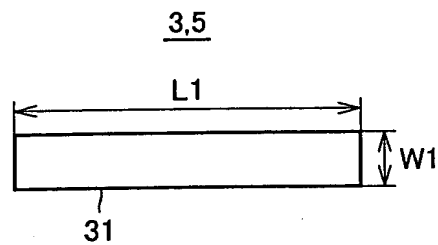


FIG. 3

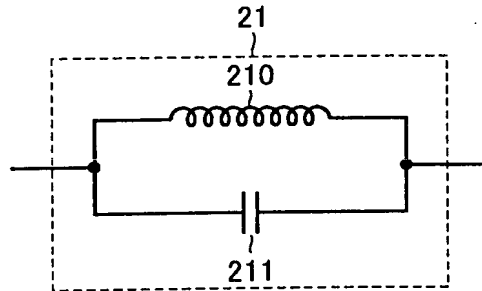


FIG. 4

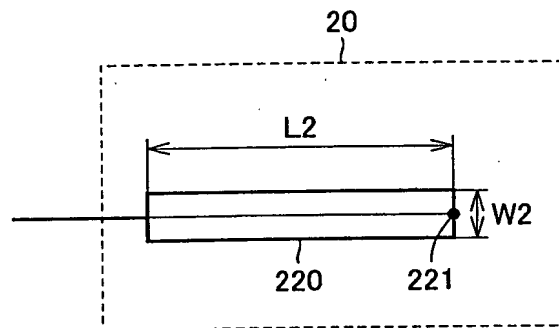


FIG. 5

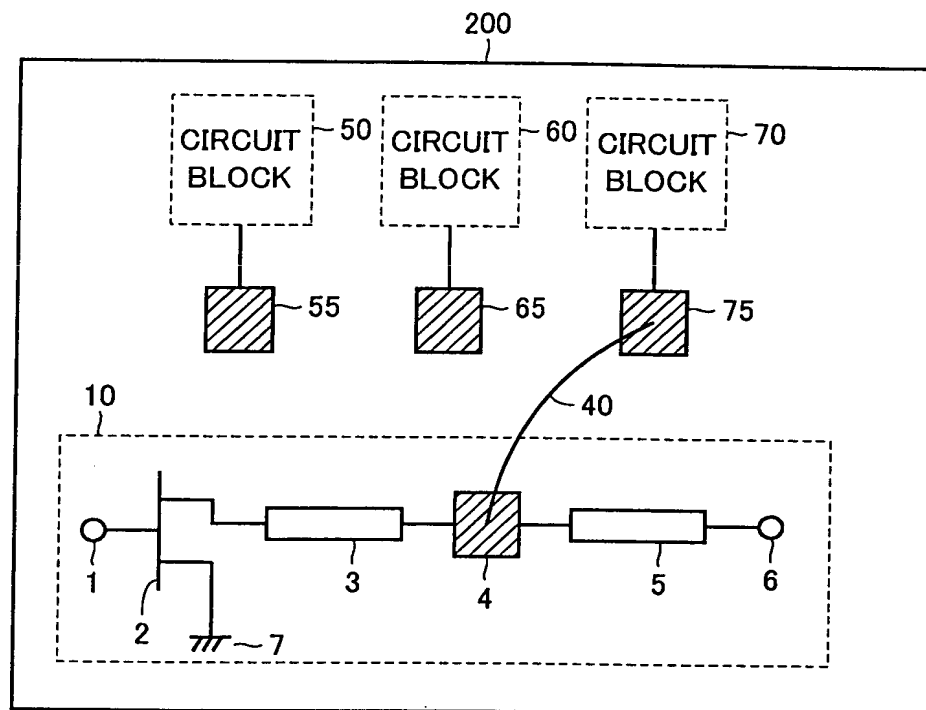
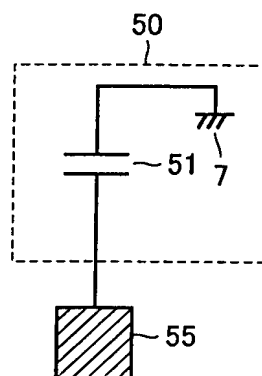


FIG. 6



Title: HIGH-FREQUENCY SEMICONDUCTOR INTEGRATED CIRCUIT CAPABLE OF SWITCHING
BETWEEN CHARACTERISTICS THE OF

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FIG. 7

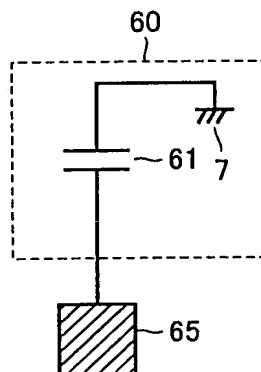


FIG. 8

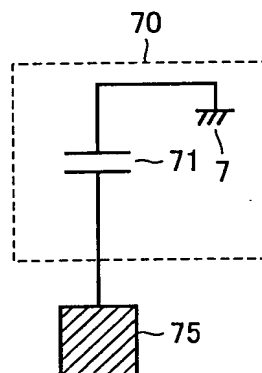


FIG. 9

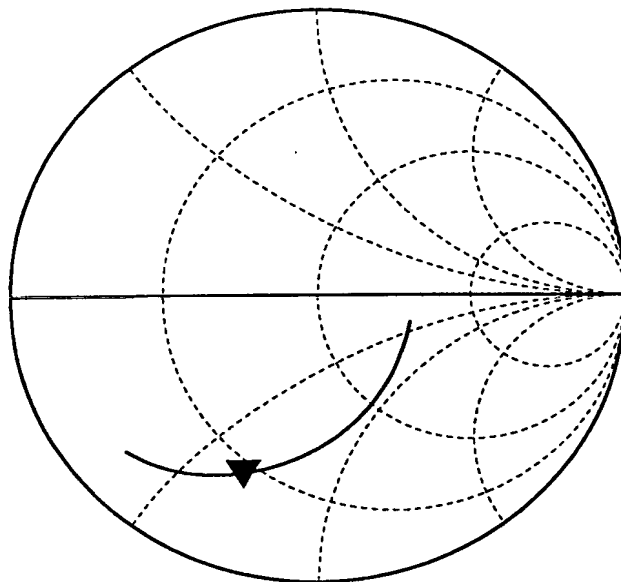


FIG. 10

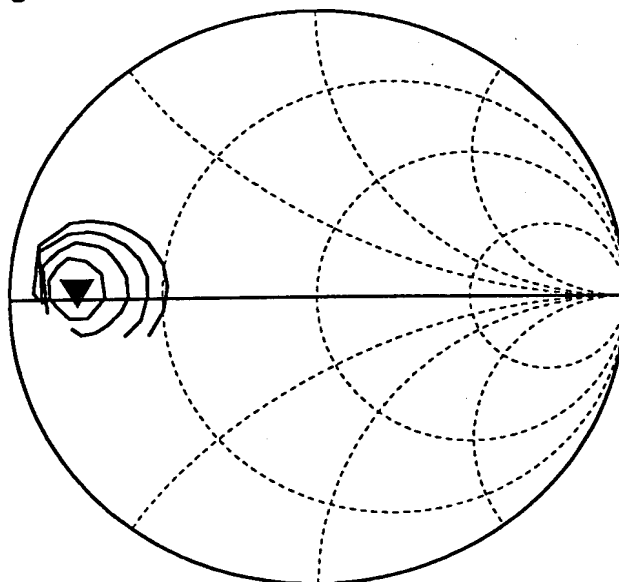


FIG. 11

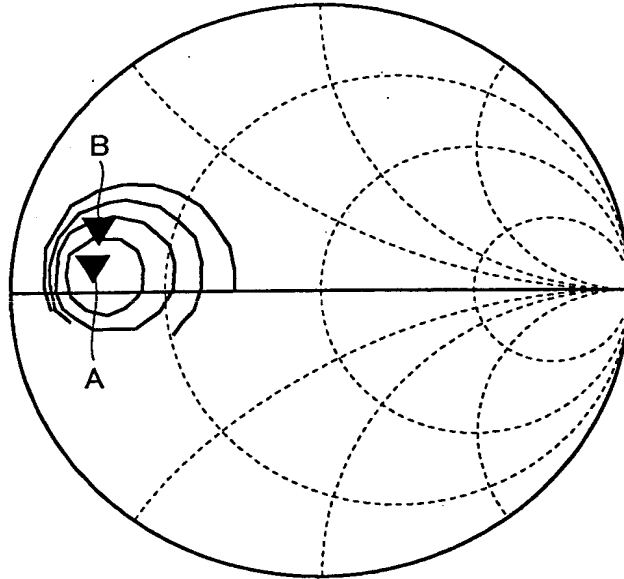


FIG. 12

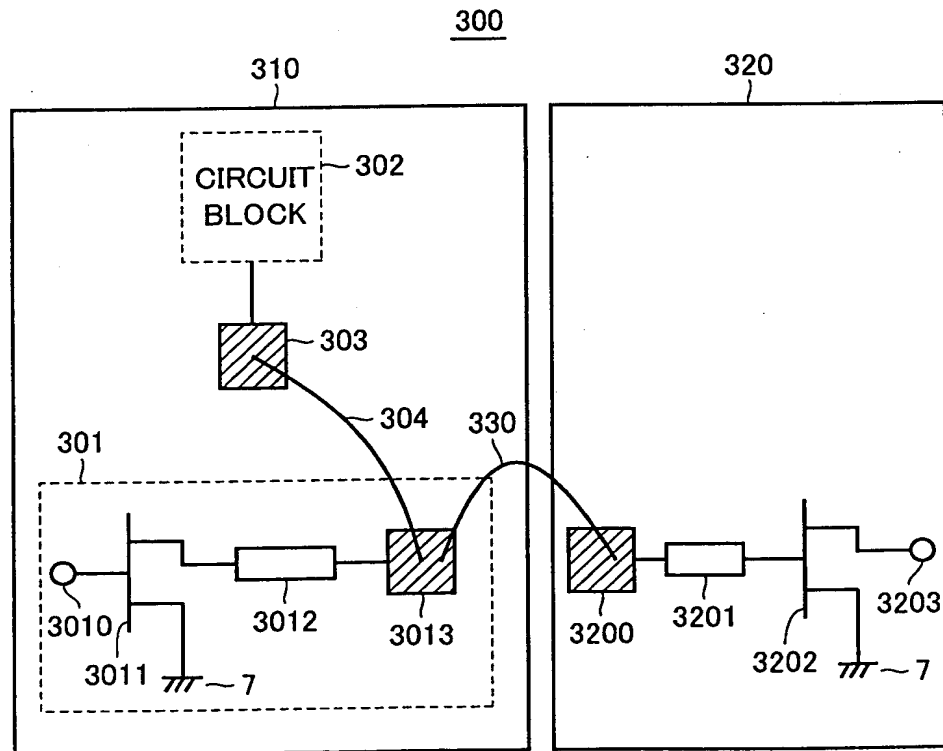


FIG. 13A

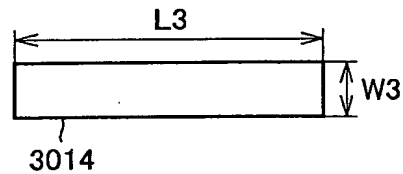


FIG. 13B

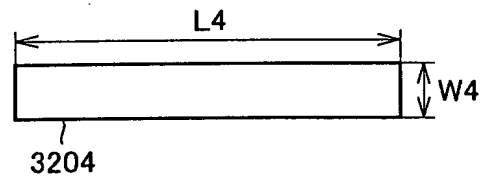
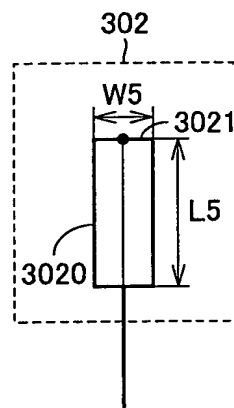


FIG. 14



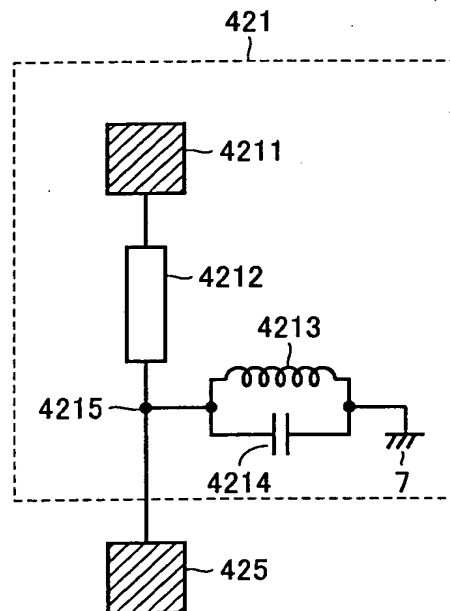


FIG. 17

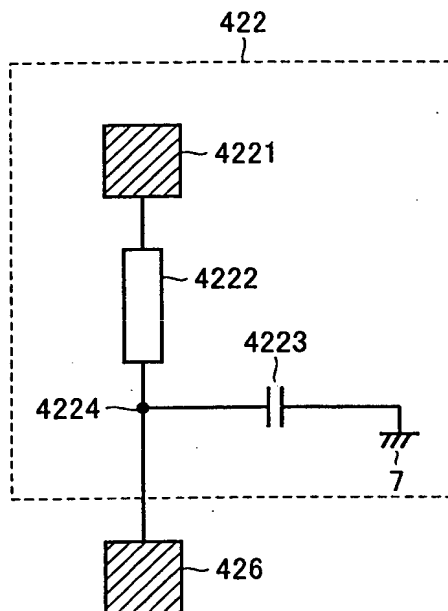


FIG. 18

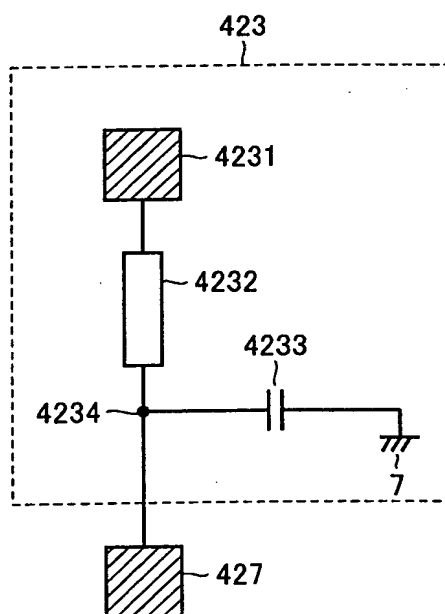


FIG. 19

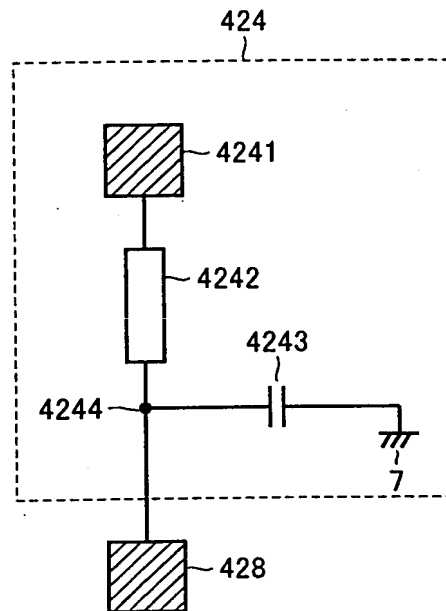


FIG. 20

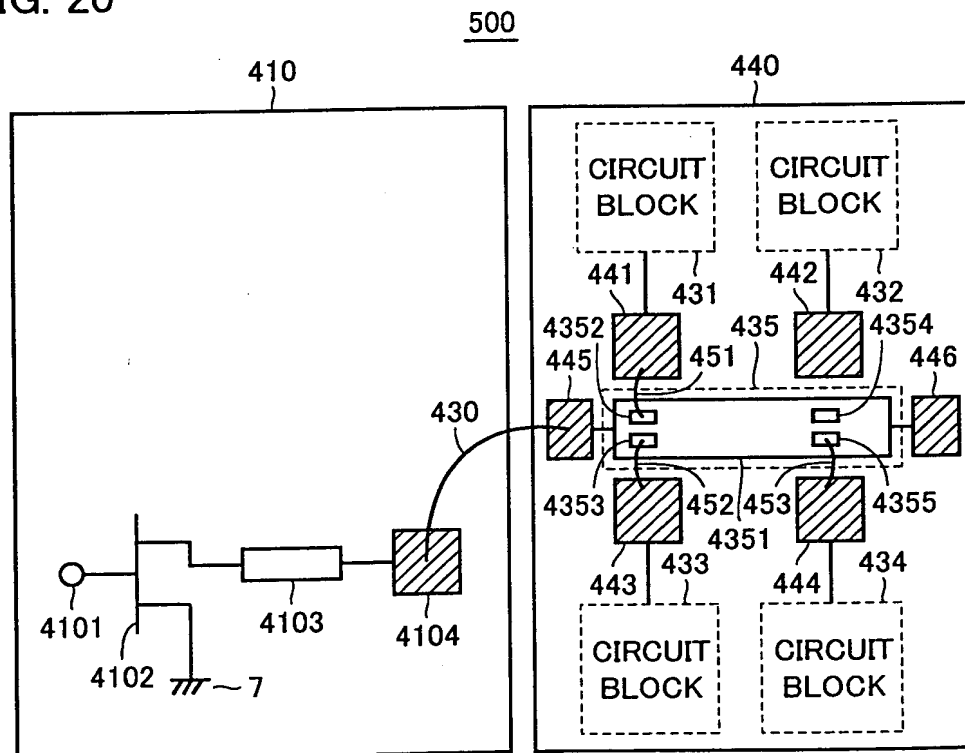
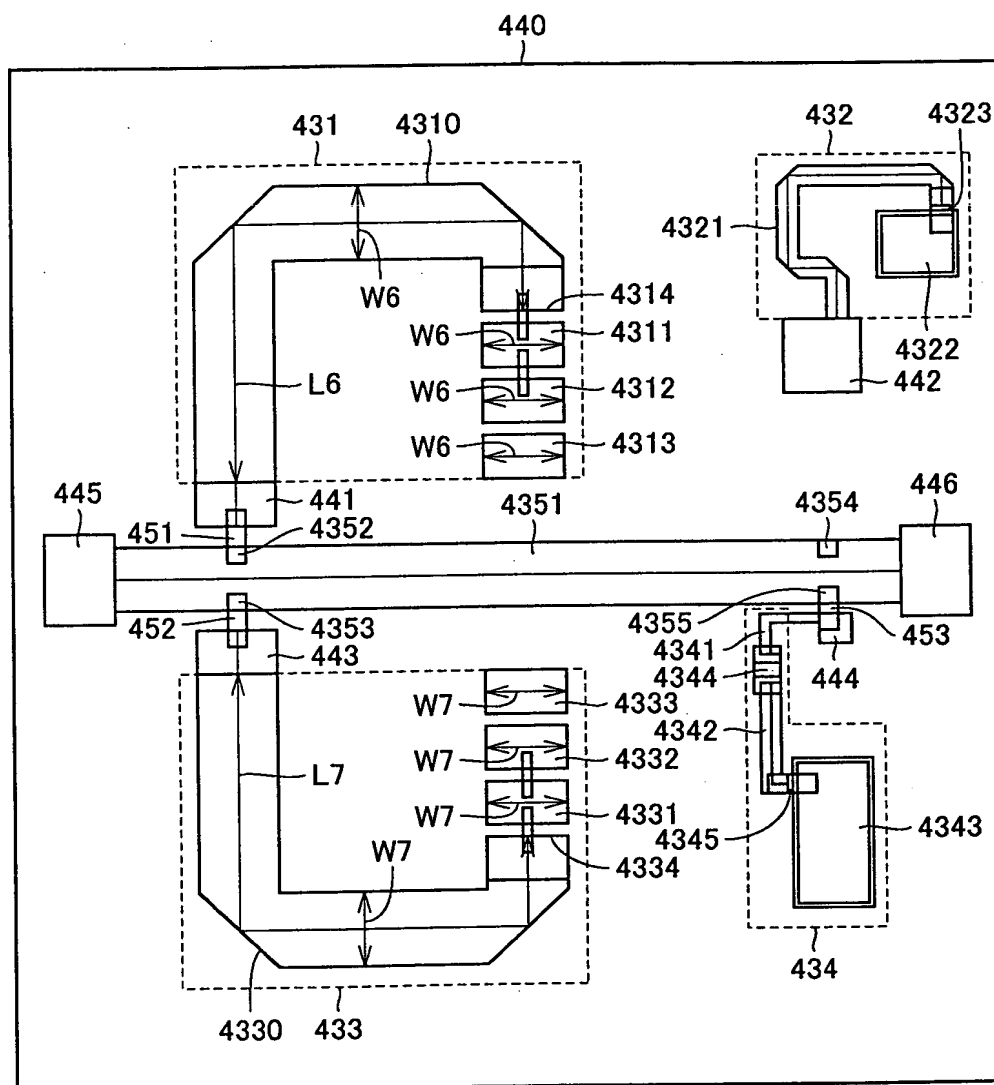


FIG. 21



Title: HIGH-FREQUENCY SEMICONDUCTOR INTEGRATED CIRCUIT CAPABLE OF SWITCHING
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FIG. 22 PRIOR ART

